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- EPIC™ (Enhanced-Performance Implanted CMOS) 2-µ Process
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC}, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 2 V at V_{CC}, T_A = 25°C
- ESD Protection Exceeds 2000 V per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Chip Carriers (FK), and (J) 300-mil DIPs

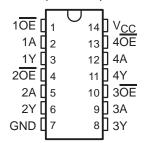
description

These quadruple bus buffer gates are designed for 2.7-V to 5.5-V $V_{\rm CC}$ operation.

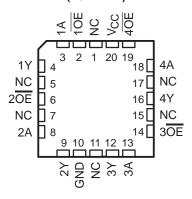
The 'LV125 feature independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (\overline{OE}) input is high.

The SN54LV125 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV125 is characterized for operation from –40°C to 85°C.

SN54LV125 . . . J OR W PACKAGE SN74LV125 . . . D, DB, OR PW PACKAGE (TOP VIEW)



SN54LV125 . . . FK PACKAGE (TOP VIEW)



NC - No internal connection

FUNCTION TABLE (each buffer)

INP	JTS	OUTPUT
OE	Α	Y
L	Н	Н
L	L	L
Н	Χ	Z



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

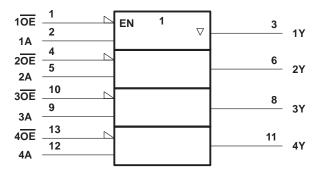
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SN54LV125, SN74LV125 QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

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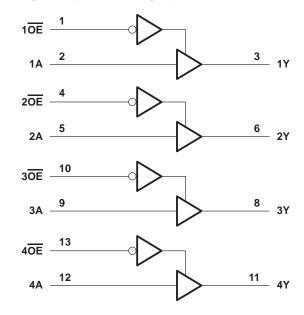
logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

Pin numbers shown are for D, DB, J, PW, and W packages.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V _{CC}	0.5 V to 7 V
Input voltage range, V _I (see Note 1)	$0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Output voltage range, V _O (see Notes 1 and 2) –0	$0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$)	±20 mA
Output clamp current, I _{OK} (V _O < 0 or V _O > V _{CC})	±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	±35 mA
Continuous current through V _{CC} or GND	±70 mA
Maximum power dissipation at T _A = 55°C (in still air) (see Note 3): D package	1.25 W
DB or PW package	0.5 W
Operating free-air temperature range, T _A	−40°C to 85°C
Storage temperature range, T _{stg}	−65°C to 150°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. This value is limited to 7 V maximum.
 - 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.



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recommended operating conditions (see Note 4)

			SN54LV125		SN74LV125		UNIT
			MIN	MAX	MIN	MAX	UNII
Vсс	Supply voltage		2.7	5.5	2.7	5.5	V
\/	High-level input voltage		2		2		V
VIH	nigii-ievei iriput voitage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	3.15		3.15		V
\/	Low-level input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8		0.8	V
VIL	Low-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		1.65		1.65	
VI	Input voltage		0	Vcc	0	VCC	V
Vo	Output voltage		0,	VCC	0	VCC	V
lau	High lovel output ourrent	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	20	-8		-8	mA
ЮН	High-level output current	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	20	-16		-16	mA
la.	Low level output ourrent	V _{CC} = 2.7 V to 3.6 V	V	8		8	mA
IOL	Low-level output current $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$			16		16	IIIA
Δt/ΔV	Input transition rise or fall rate		0	100	0	100	ns/V
TA	Operating free-air temperature		-55	125	-40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST CONDITIONS	V +	SN54	LV125	SN				
PARAMETER	TEST CONDITIONS	v _{cc} †	MIN T	YP [†] MAX	MIN	TYP [†]	MAX	UNIT	
^V OH	I _{OH} = -100 μA	MIN to MAX‡	V _{CC} -0.2		V _{CC} -0.	2			
	$I_{OH} = -8 \text{ mA}$	3 V	2.4		2.4			V	
	I _{OH} = - 16 mA	4.5 V	3.6		3.6				
	I _{OL} = 100 μA	MIN to MAX‡		0.2			0.2		
VOL	I _{OL} = 8 mA	3 V		0.4			0.4	V	
	I _{OL} = 16mA	4.5 V		0.55			0.55		
1.	V _I = V _{CC} or GND	3.6 V		±1			±1		
lj		5.5 V		±1			±1	μΑ	
lo=	$V_O = V_{CC}$ or GND	3.6 V	1	±5			±5	μΑ	
loz		5.5 V	3	±5			±5	μΑ	
loo	V: Vocar CND	3.6 V	30	20			20	μΑ	
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V	9	20			20	μΑ	
∆lCC	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 3.6 V		500			500	μΑ	
0:	V - V CNID	3.3 V		3.5		3.5		pF	
C _i	V _I = V _{CC} or GND	5 V		3.5		3.5			
0	V V == CND	3.3 V		8		8			
Co	$V_O = V_{CC}$ or GND	5 V		8		8		pF	

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

[‡] For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

SN54LV125, SN74LV125 QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

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switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

							SN54	LV125				
	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V	сс = 5.5 ± 0.5 V	V	V	± 0.3 V	٧	V _{CC} =	2.7 V	UNIT
				MIN	TYP	MAX	MIN	TYP†	MAX	∴ MIN	MAX	
	^t pd	А	Y		7	18	N.S.	9	19	677	23	ns
	^t en	ŌĒ	Y		5	19		7	25	7	31	ns
	^t dis	ŌĒ	Y		7	17		9	23		28	ns

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

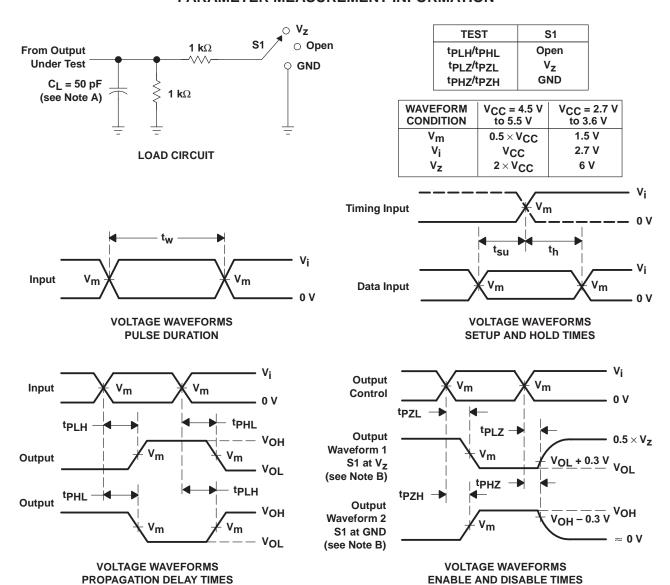
						SN74	LV125				
PARAMETER	FROM TO (OUTPUT)		V _{CC} = 5.5 V ± 0.5 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 2.7 V		UNIT		
			MIN	TYP	MAX	MIN	TYP†	MAX	MIN	MAX	
^t pd	А	Υ		7	18		9	19		23	ns
^t en	ŌĒ	Y		5	19		7	25		31	ns
^t dis	ŌĒ	Y		7	17		9	23		28	ns

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

operating characteristics, T_A = 25°C

	PARAMETER		TEST CONDITIONS	VCC	TYP	UNIT
C _{pd} Power dissipation capacitance	Outputs enabled		3.3 V	45	pF	
	Outputs disabled	C _I = 50 pF, f = 10 MHz		5		
	rower dissipation capacitance	Outputs enabled	C[= 30 pr, 1 = 10 WH12	5 V	48	pF
		Outputs disabled			5	pr

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.

LOW- AND HIGH-LEVEL ENABLING

- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.

INVERTING AND NONINVERTING OUTPUTS

- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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